

Device Modeling Report

COMPONENTS: Power MOSFET (Professional)
PART NUMBER: TPCF8302
MANUFACTURER: TOSHIBA
Body Diode (Professional) / ESD Protection Diode



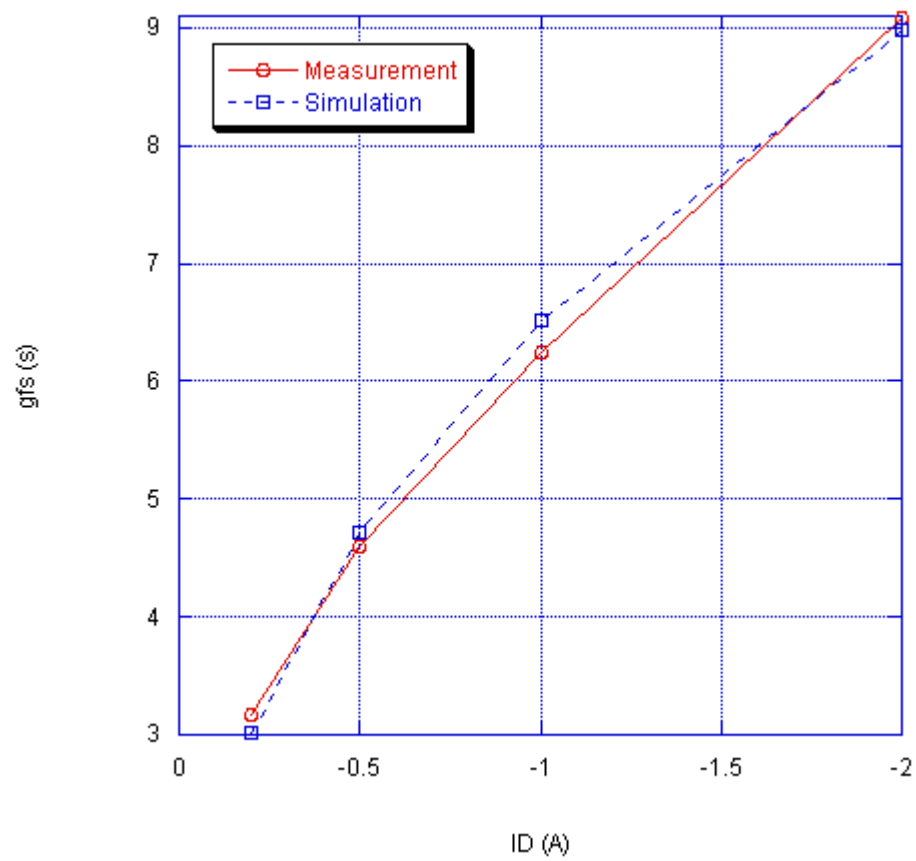
Bee Technologies Inc.

MOSFET MODEL

Pspice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Modility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Transconductance Characteristic

Circuit Simulation Result

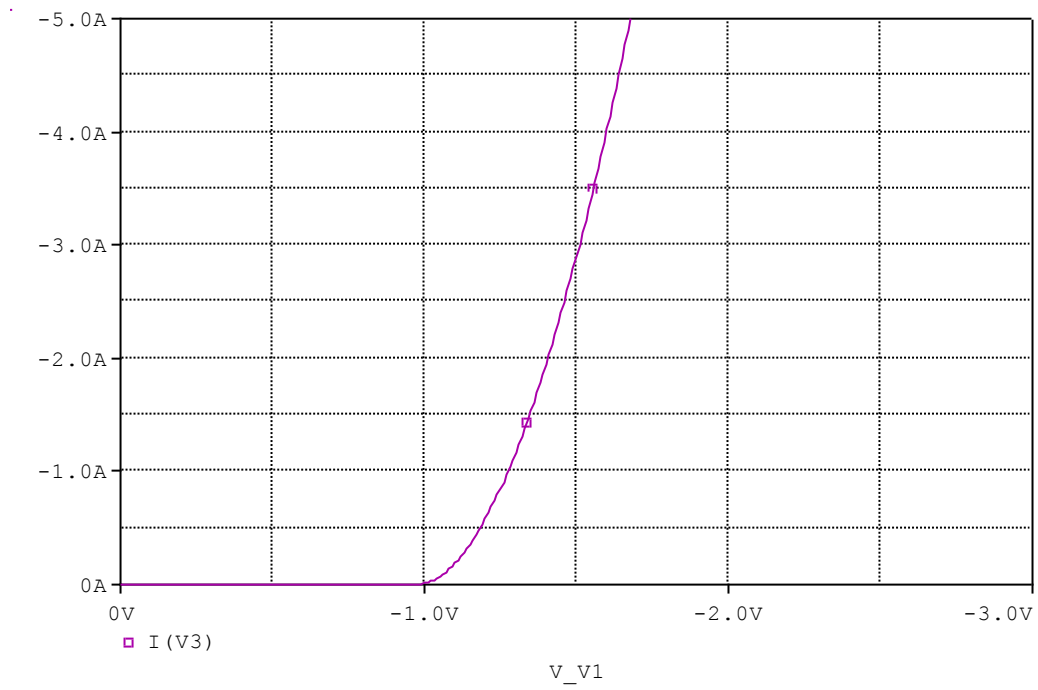


Simulation Result

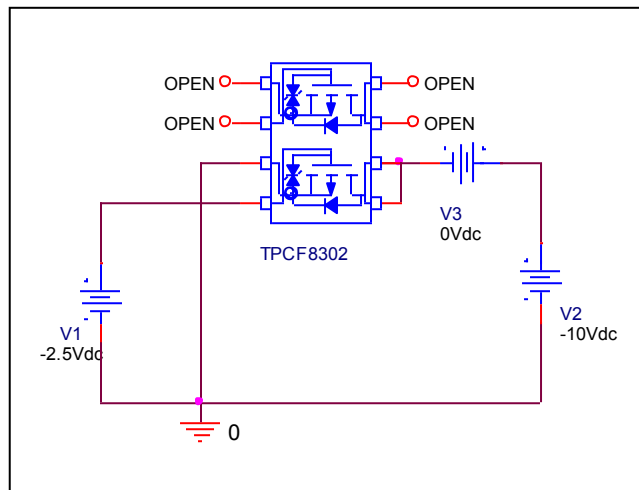
ID(A)	VGS(V)		Error (%)
	Measurement	Simulation	
-0.200	3.170	3.017	-4.826
-0.500	4.600	4.717	2.543
-1.000	6.250	6.519	4.304
-2.000	9.090	8.980	-1.210

V_{gs}-I_d Characteristic

Circuit Simulation result

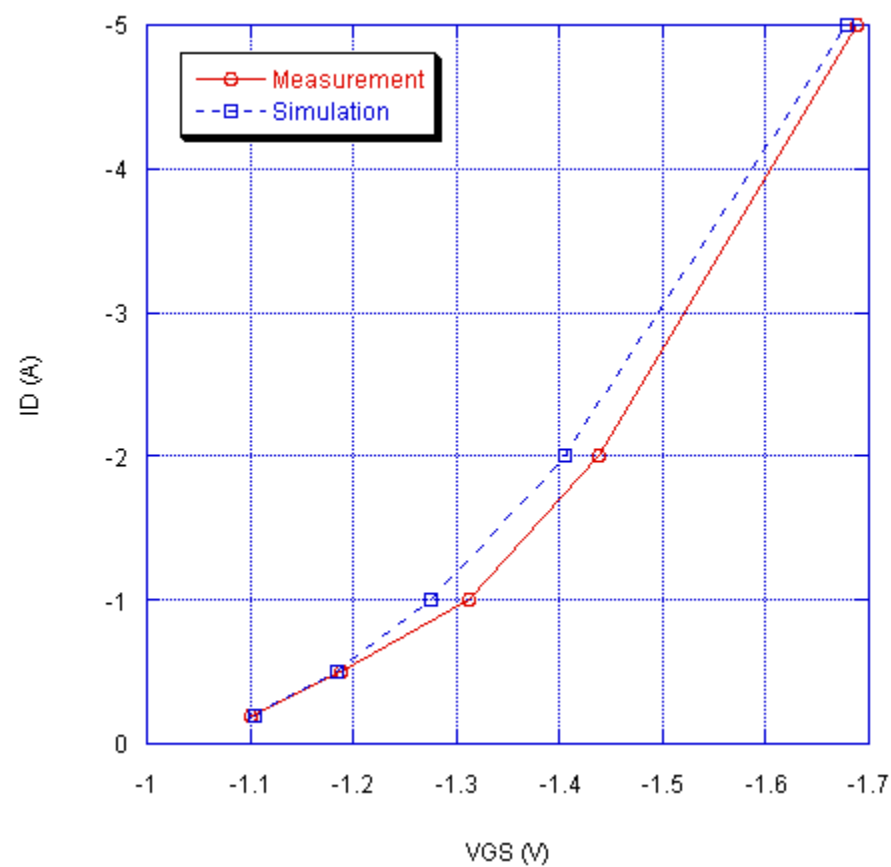


Evaluation circuit



Comparison Graph

Circuit Simulation Result

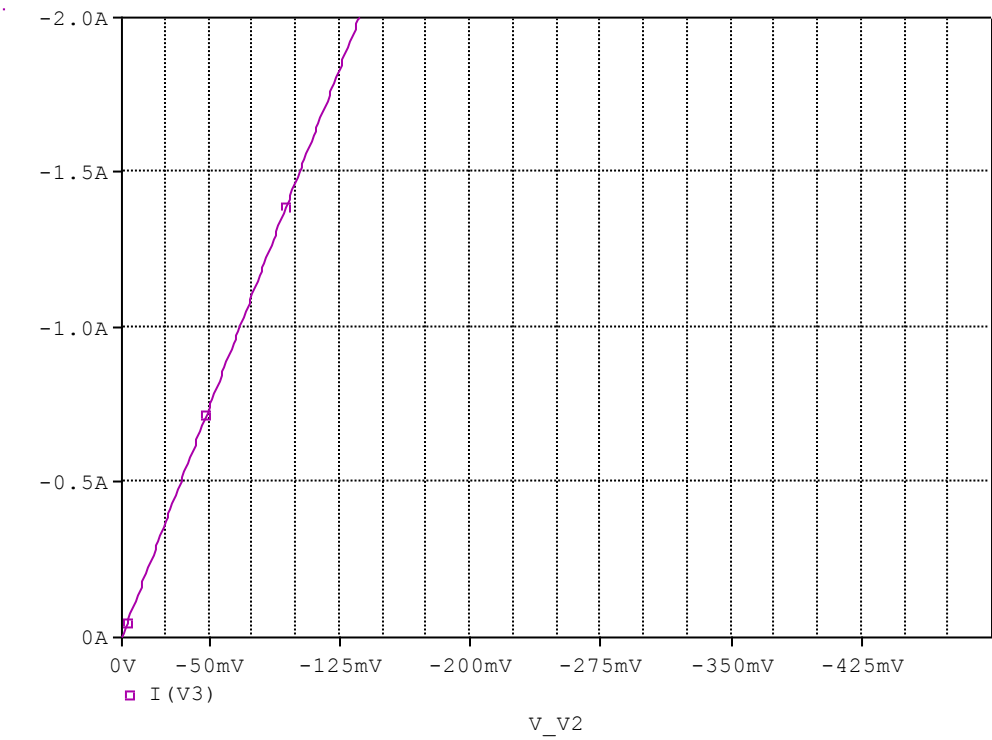


Simulation Result

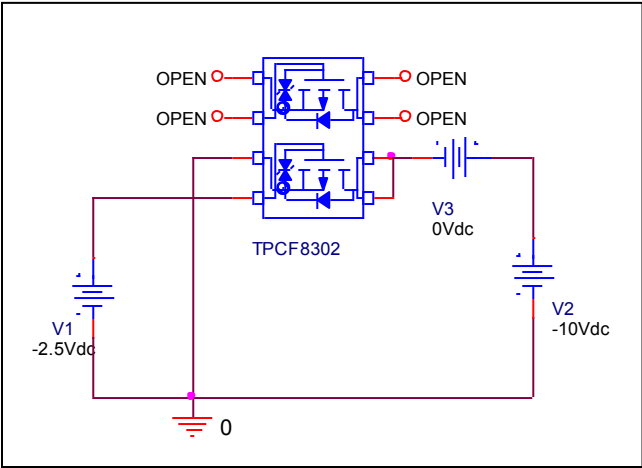
I_D (A)	V_{GS} (V)		Error (%)
	Measurement	Simulation	
-0.200	-1.100	-1.105	0.427
-0.500	-1.188	-1.184	-0.320
-1.000	-1.313	-1.275	-2.895
-2.000	-1.438	-1.406	-2.191
-5.000	-1.688	-1.678	-0.575

Id-Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

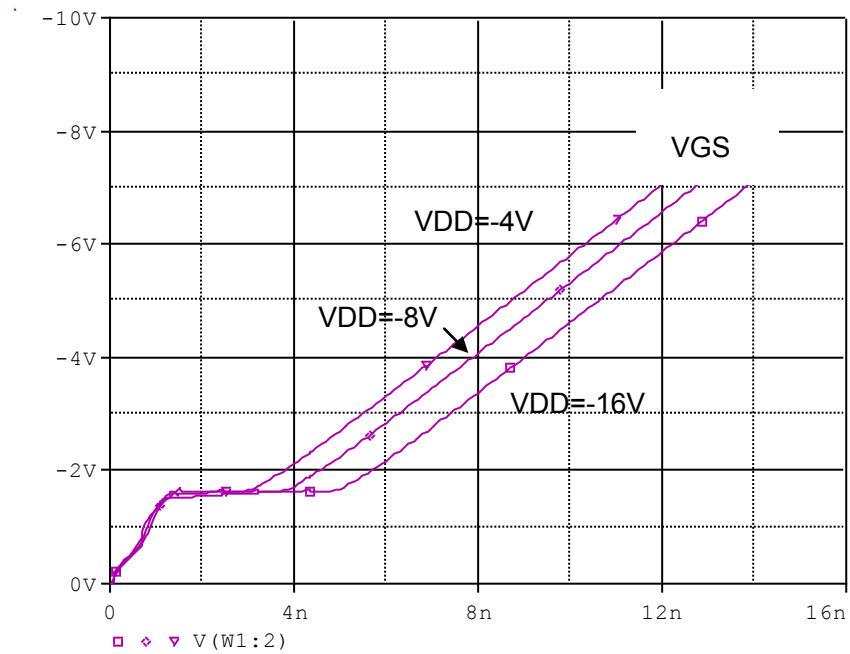


Simulation Result

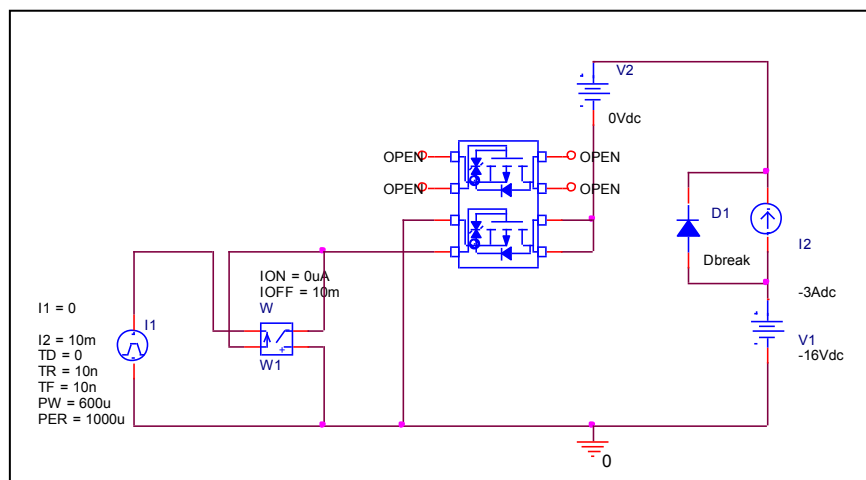
$I_D = -1.5, V_{GS} = -2.5V$	Measurement		Simulation		Error (%)
$R_{DS} (on)$	68	mΩ	68	mΩ	0

Gate Charge Characteristic

Circuit Simulation result



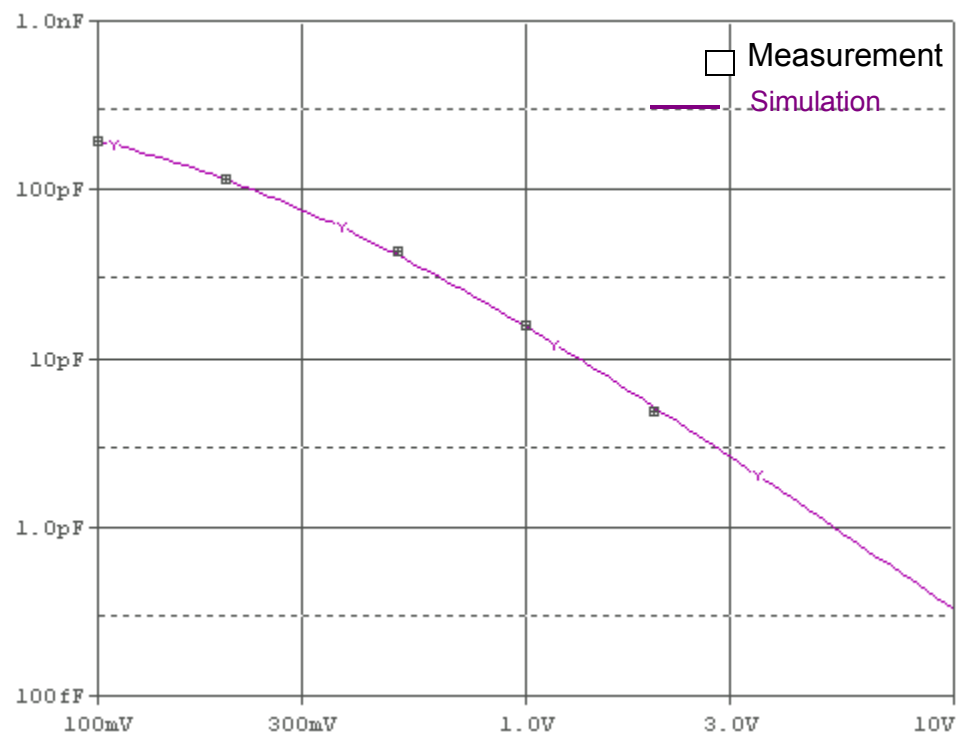
Evaluation circuit



Simulation Result

$V_{DD} = -8V, I_D = -3A$ $V_{GS} = -5V$	Measurement		Simulation		Error (%)
Q_{gs}	1.30	nC	1.3	nC	0.000
Q_{gd}	2.60	nC	2.61	nC	0.385
Q_g	9.50	nC	9.52	nC	0.211

Capacitance Characteristic

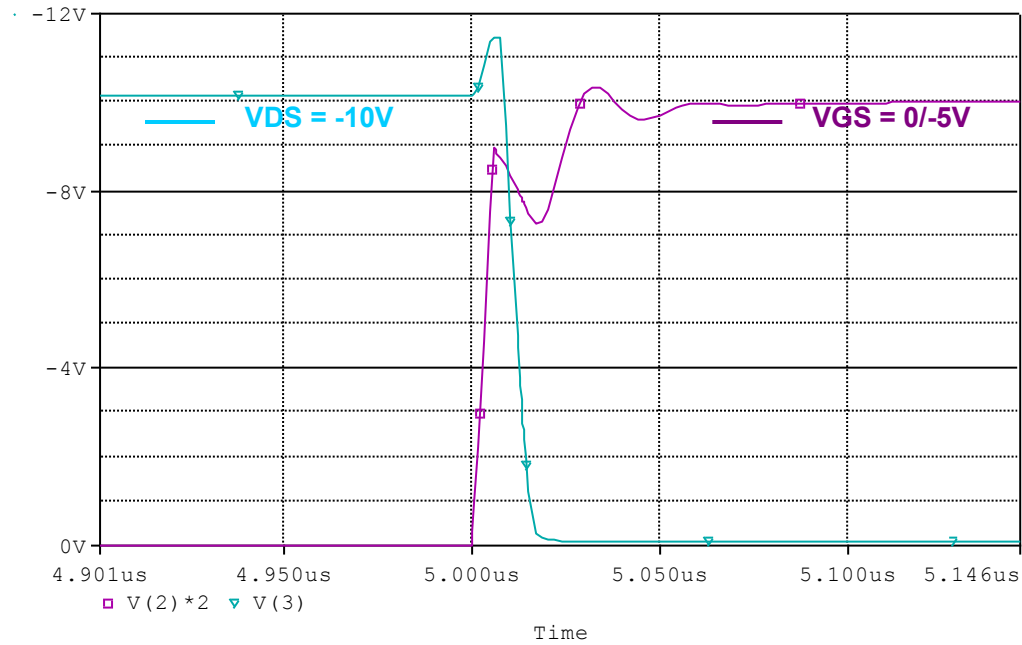


Simulation Result

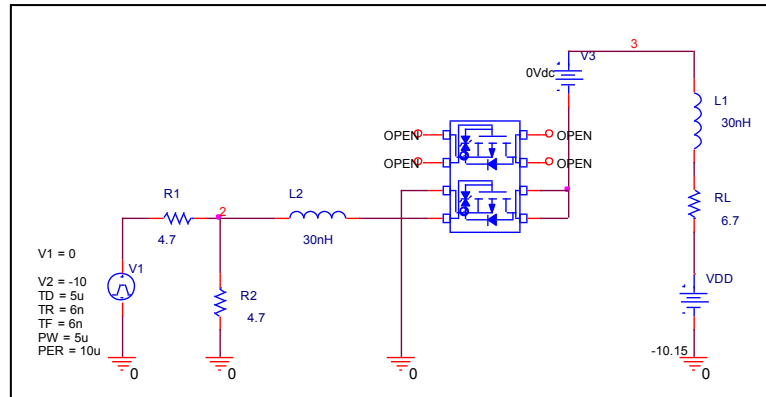
V _{DS} (V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.100	200.000	194.000	-3.000
0.200	120.000	117.000	-2.500
0.500	44.000	42.000	-4.545
1.000	16.000	16.000	0.000
2.000	5.000	5.200	4.000

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

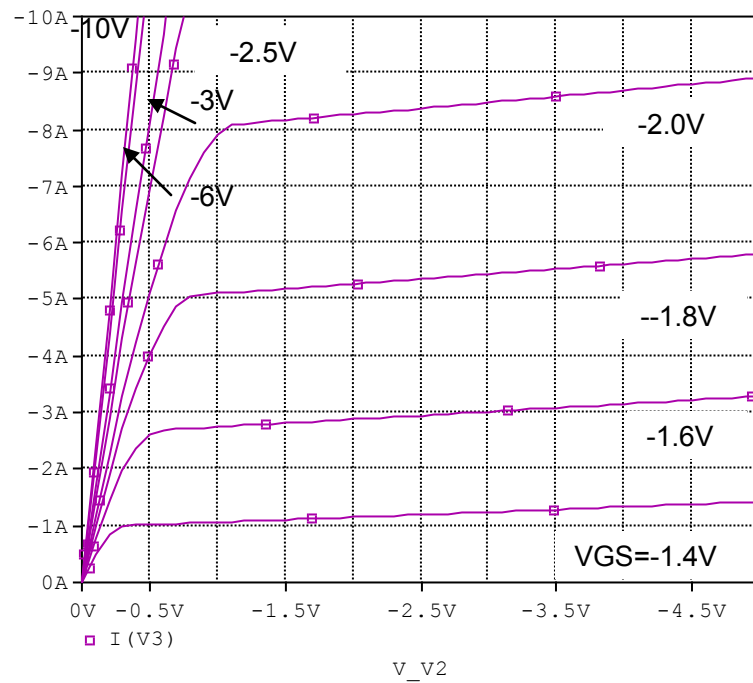


Simulation Result

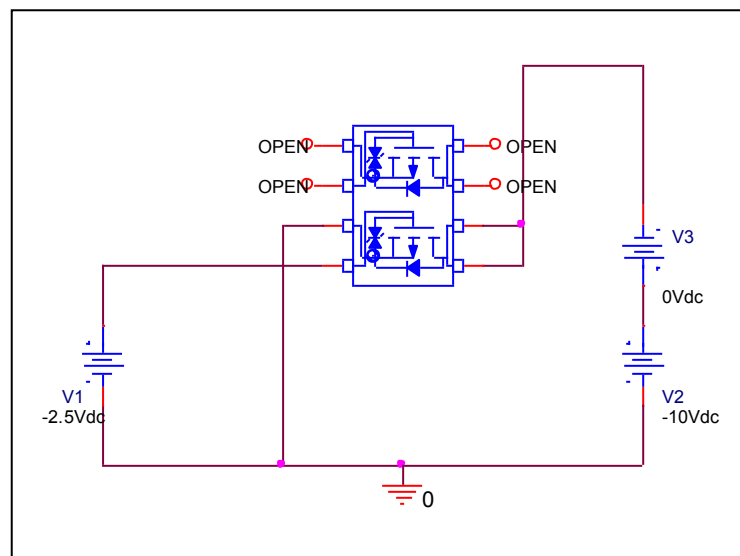
$I_D = -1.5A$, $V_{DD} = -10V$ $V_{GS} = 0/-5V$	Measurement		Simulation		Error(%)
ton	15.000	ns	14.988	ns	-0.080

Output Characteristic

Circuit Simulation result

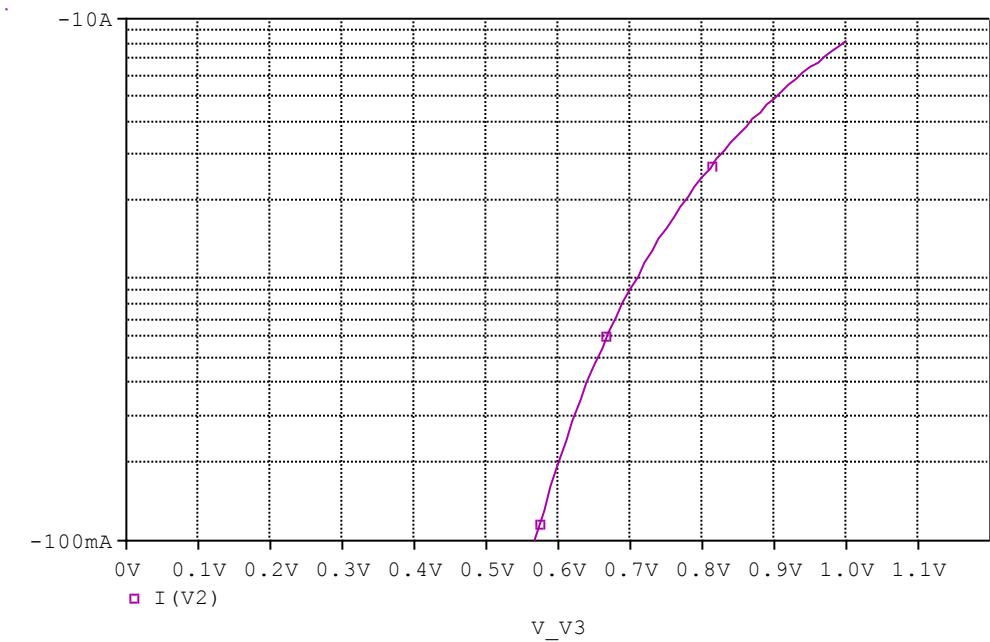


Evaluation circuit

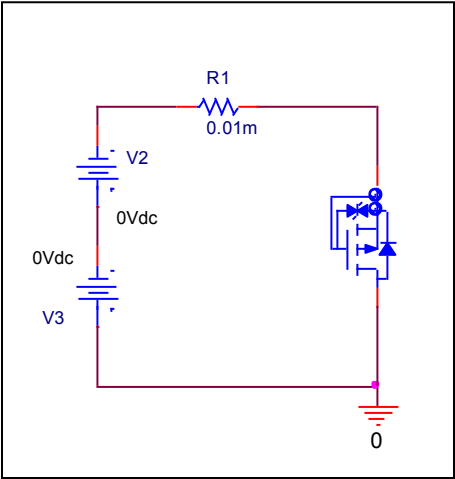


Forward Current Characteristic

Circuit Simulation Result

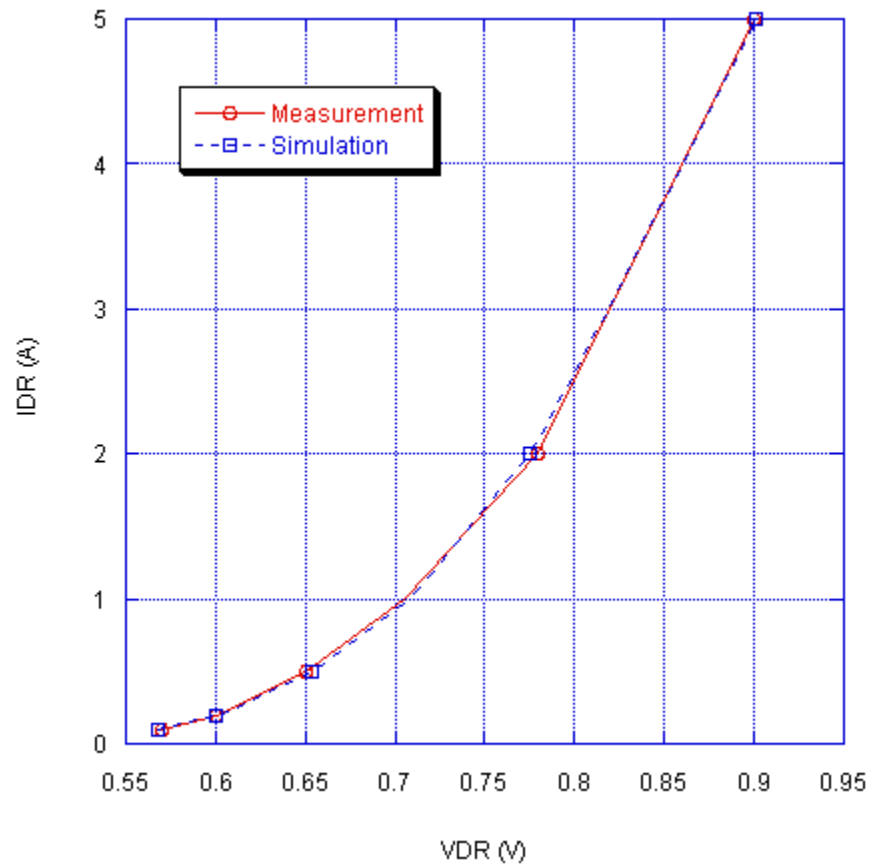


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

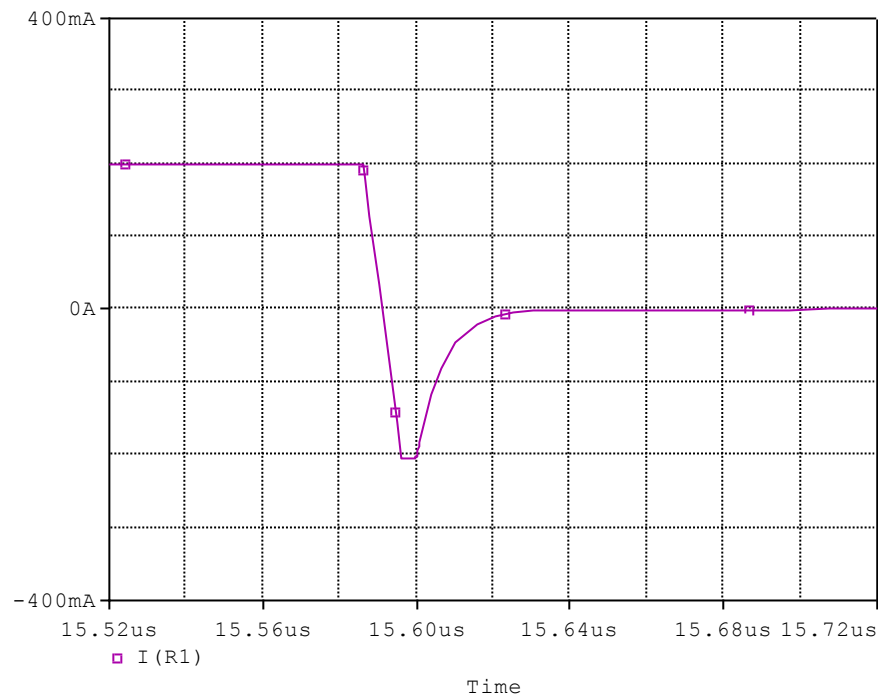


Simulation Result

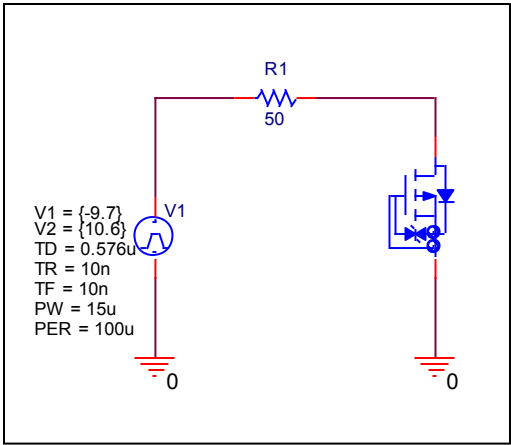
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.100	0.570	0.568	-0.439
0.200	0.600	0.600	0.050
0.500	0.650	0.654	0.569
1.000	0.705	0.707	0.270
2.000	0.780	0.775	-0.641
5.000	0.900	0.901	0.133

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

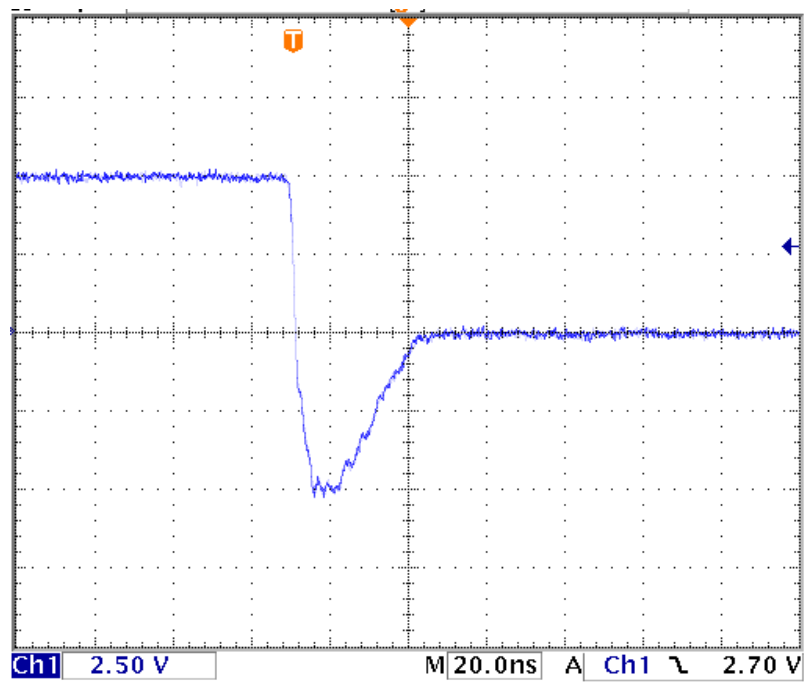


Compare Measurement vs. Simulation

	Measurement		Simulation		Error(%)
trj	4.500	ns	4.539	ns	0.867
trb	19.600	ns	19.773	ns	0.883
trr	24.100	ns	24.312	ns	0.880

Reverse Recovery Characteristic

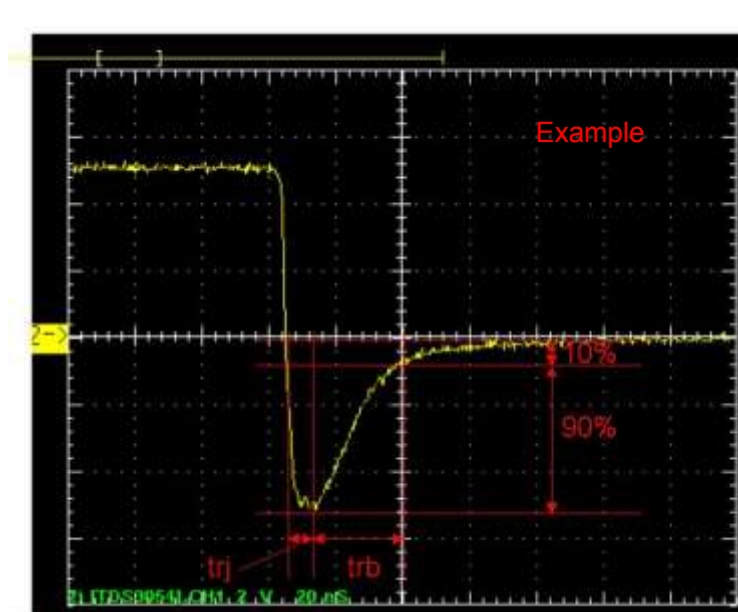
Reference



$T_{rj}=4.0(\text{ns})$

$T_{rb}=19.6(\text{ns})$

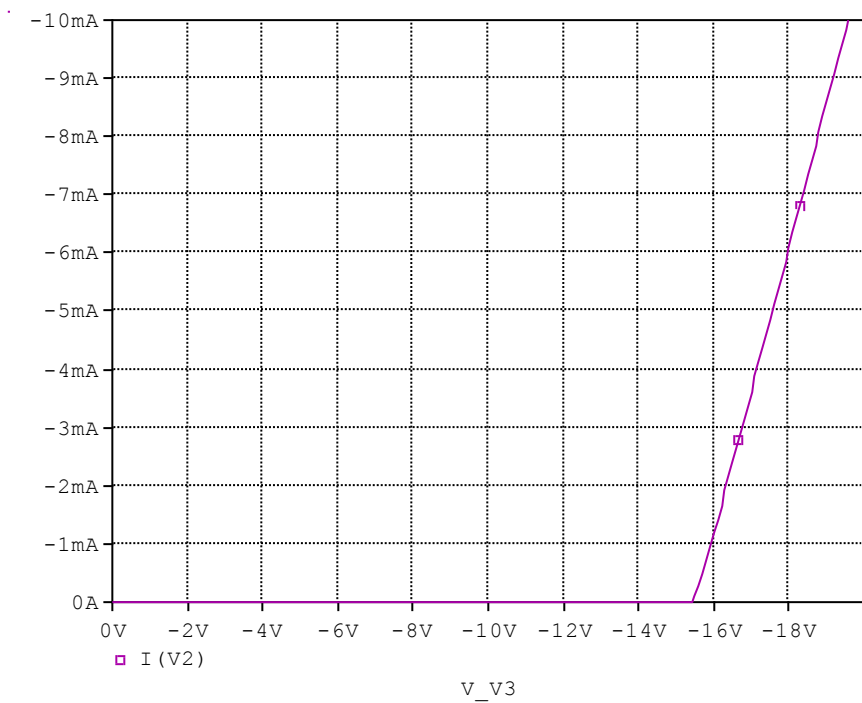
Conditions: $I_{fwd}=I_{rev}=0.2(\text{A})$, $R_L=50$



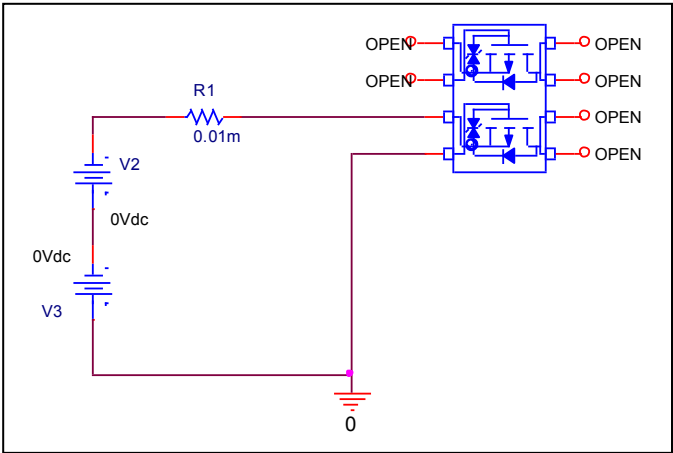
Relation between t_{rj} and t_{rb}

Zener Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



Zener Voltage Characteristic

Reference

